



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
100V	23mΩ @ V _{GS} = 10V	42A
	30mΩ @ V _{GS} = 6V	38A
	45mΩ @ V _{GS} = 4.5V	33A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Additional Tin-Plated on Sidewall Pads for Optical Solder Inspection

Description and Applications

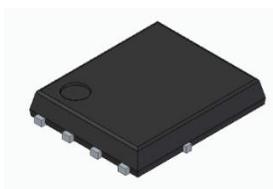
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC converters
- Motors

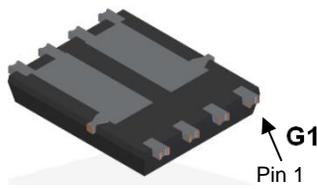
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.097 grams (Approximate)

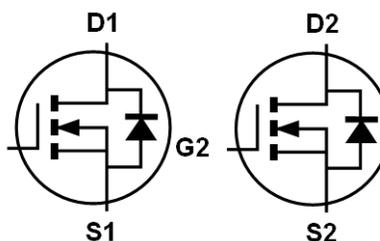
PowerDI5060-8/SWP (Type UXD)



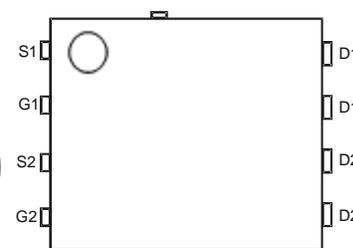
Top View



Bottom View



Equivalent Circuit



Top View
Pin Configuration

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	I _D	T _C = +25°C	42
		T _C = +100°C	30
Maximum Body Diode Forward Current	I _S	42	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	168	A
Pulsed Body Diode Forward Current (10μs Pulse, T _C = +25°C, Package Limited)	I _{SM}	168	A
Avalanche Current, L = 0.1mH	I _{AS}	20.7	A
Avalanche Energy, L = 0.1mH	E _{AS}	21.4	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	44	°C/W
Total Power Dissipation	P _D	3.4	W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	1.6	°C/W
Total Power Dissipation	P _D	93	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Notes: 5. Thermal resistance from junction to solder point (on the exposed drain pin).
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	16	23	mΩ	V _{GS} = 10V, I _D = 20A
		—	20	30		V _{GS} = 6V, I _D = 12A
		—	27	45		V _{GS} = 4.5V, I _D = 10A
Diode Forward Voltage	V _{SD}	—	0.9	1.3	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1463	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	258	—		
Reverse Transfer Capacitance	C _{rss}	—	19	—		
Gate Resistance	R _g	—	0.97	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	22	—	nC	V _{DD} = 50V, I _D = 20A V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	6.5	—		
Gate-Drain Charge	Q _{gd}	—	2.5	—		
Turn-On Delay Time	t _{D(ON)}	—	4.6	—	ns	V _{DD} = 50V, V _{GS} = 10V I _D = 20A, R _g = 6Ω
Turn-On Rise Time	t _R	—	4.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	21.3	—		
Turn-Off Fall Time	t _F	—	7.8	—		
Reverse-Recovery Time	t _{RR}	—	42	—	ns	I _F = 20A, di/dt = 100A/μs
Reverse-Recovery Charge	Q _R	—	57	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

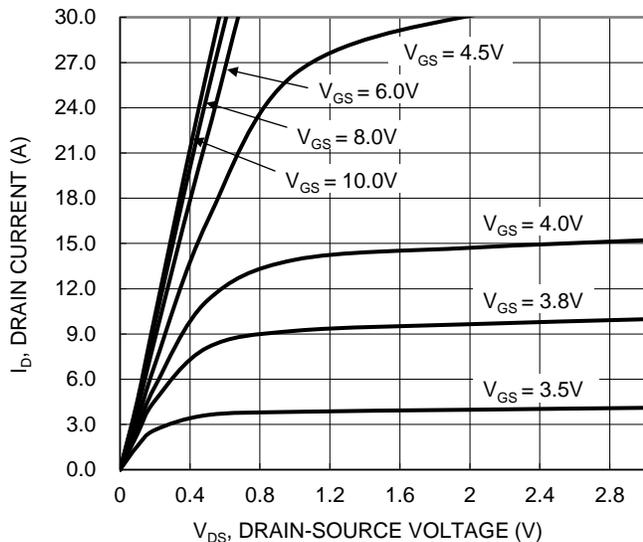


Figure 1. Typical Output Characteristic

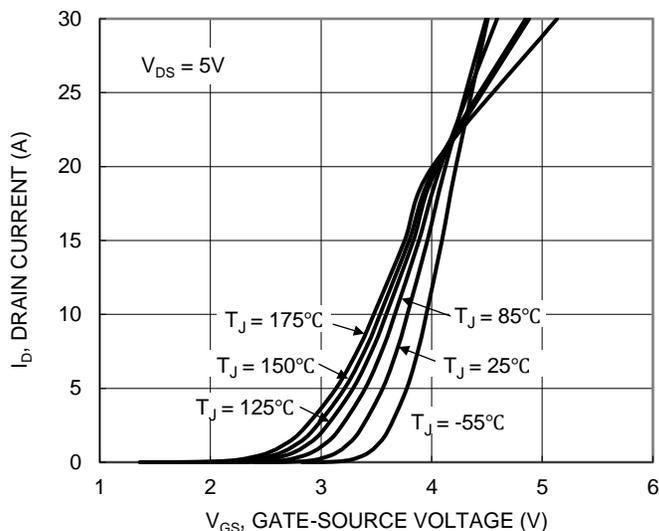


Figure 2. Typical Transfer Characteristic

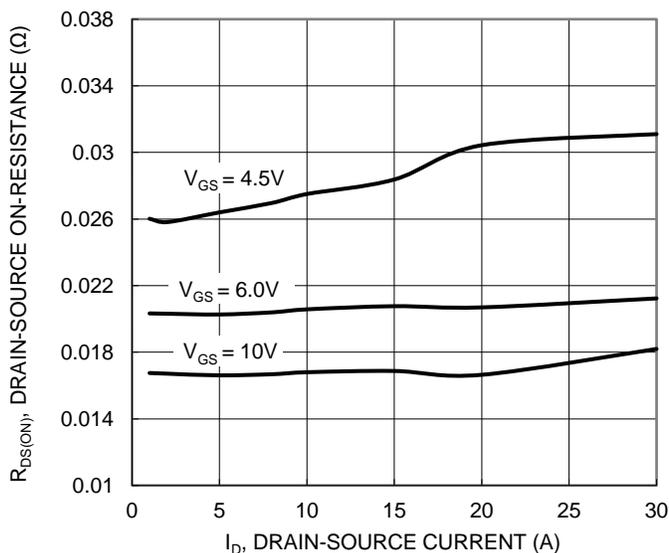


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

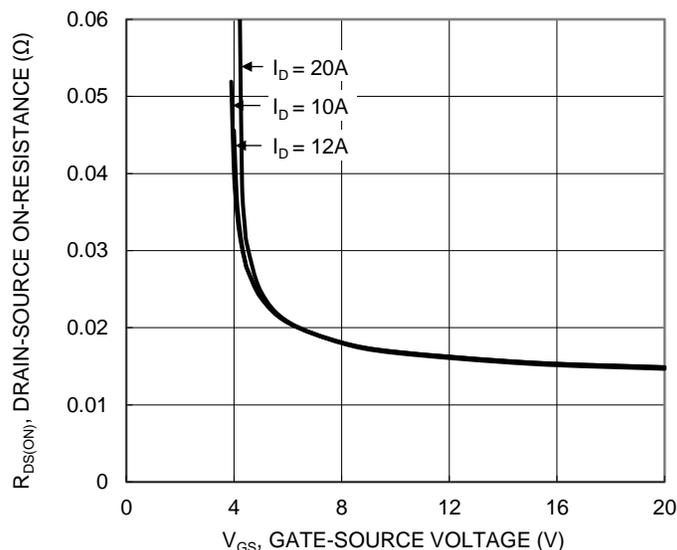


Figure 4. Typical Transfer Characteristic

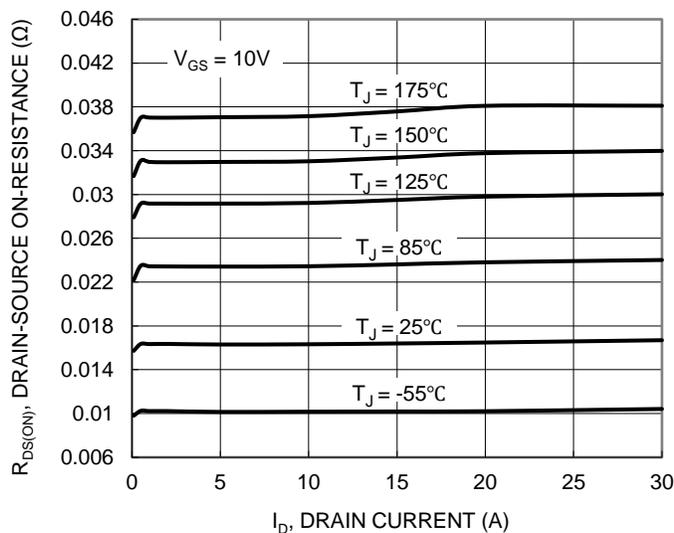


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

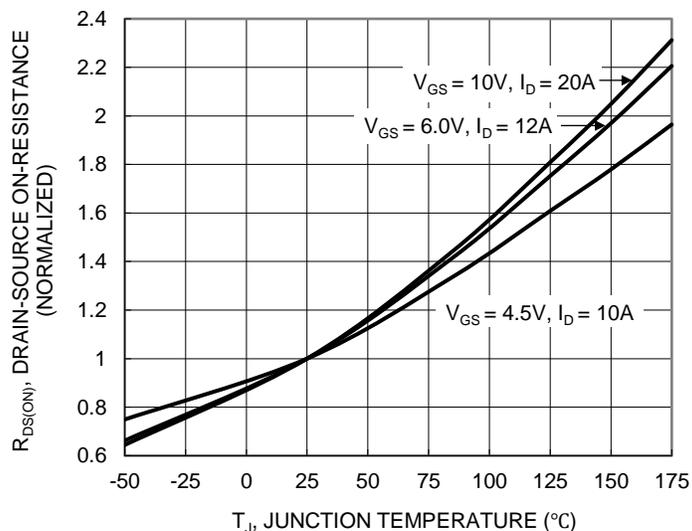


Figure 6. On-Resistance Variation with Junction Temperature

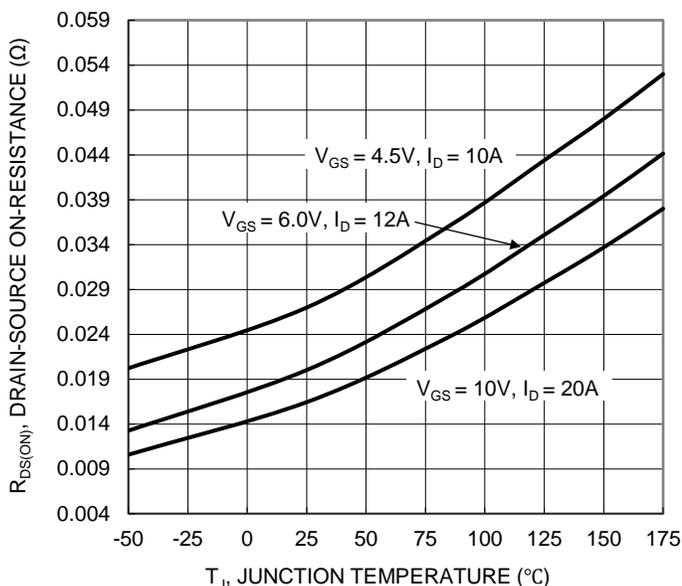


Figure 7. On-Resistance Variation with Junction Temperature

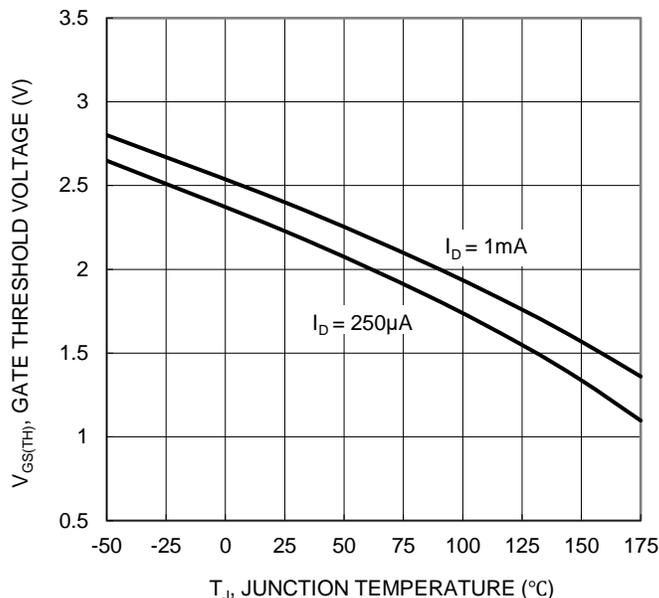


Figure 8. Gate Threshold Variation vs. Junction Temperature

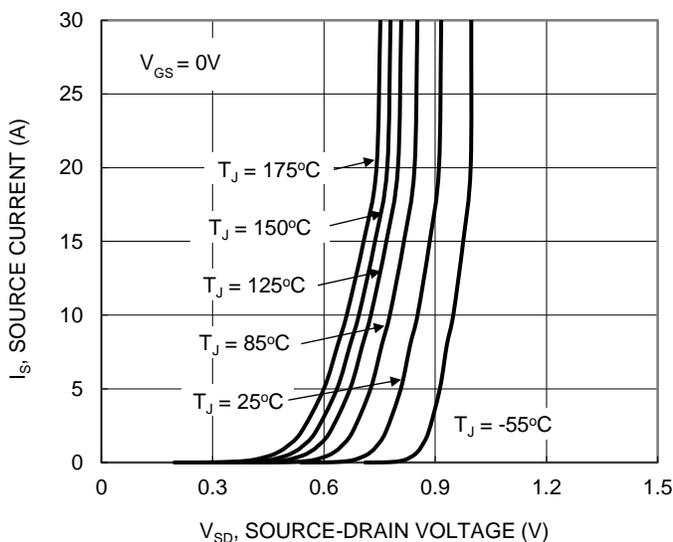


Figure 9. Diode Forward Voltage vs. Current

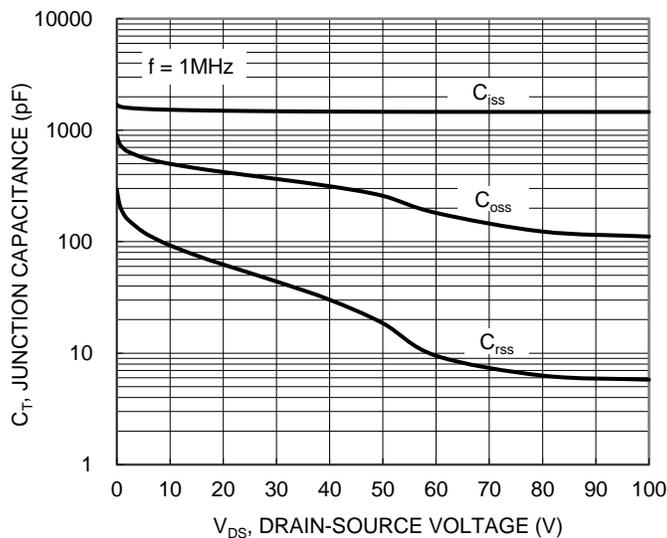
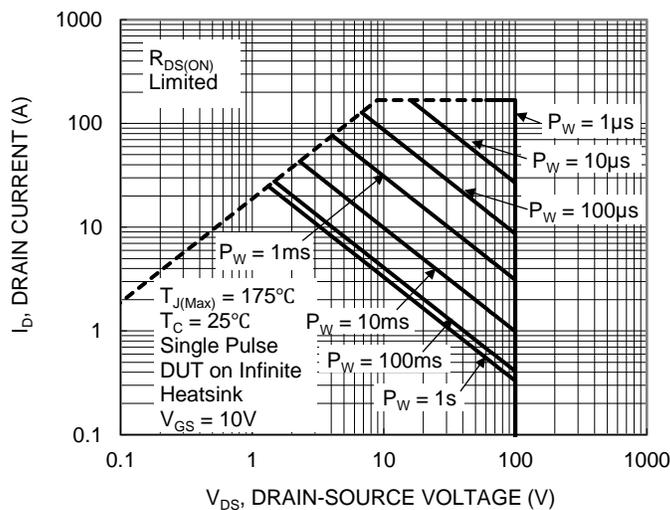
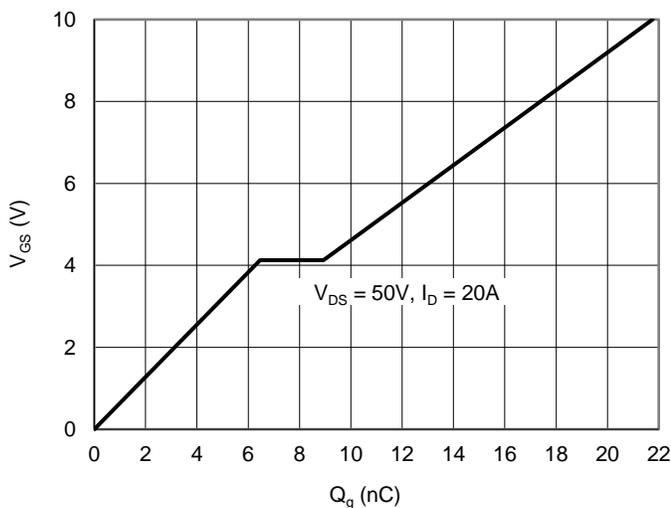


Figure 10. Typical Junction Capacitance



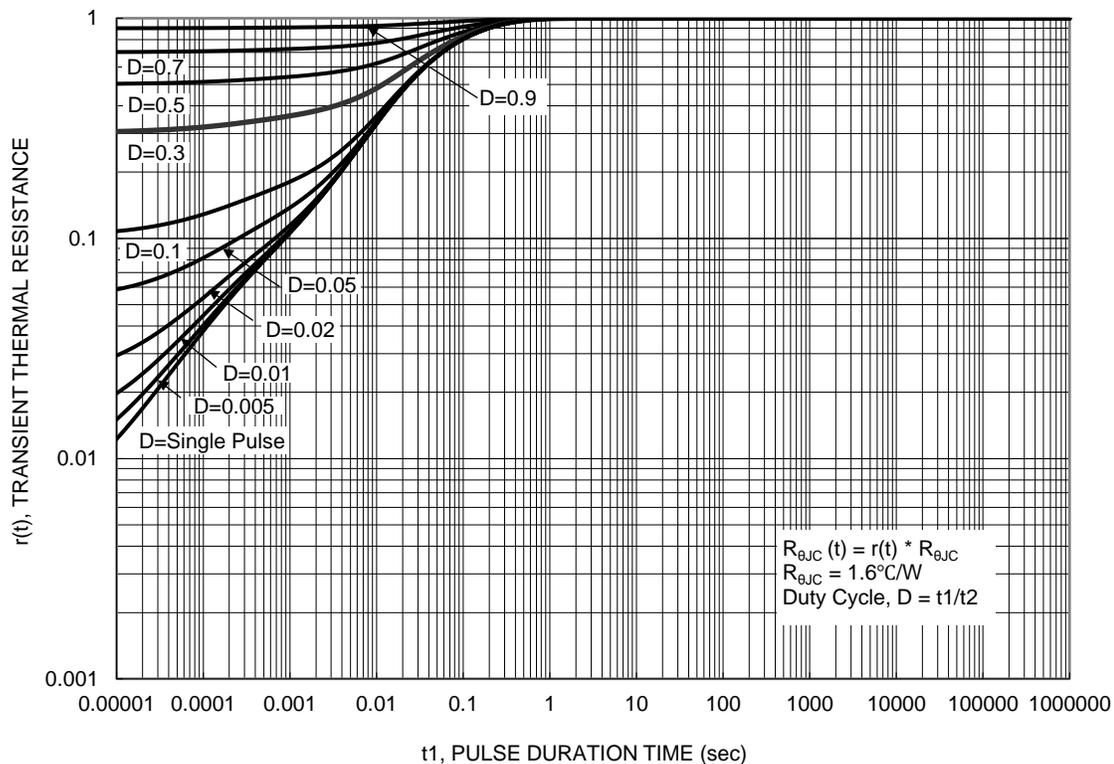
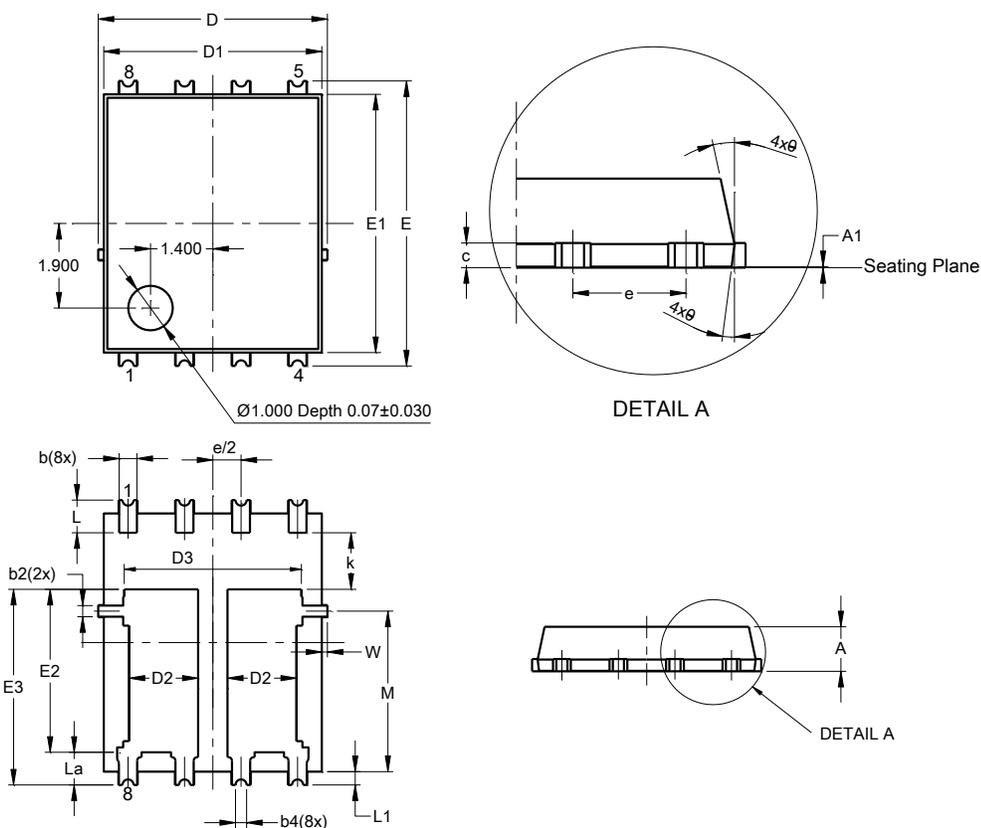


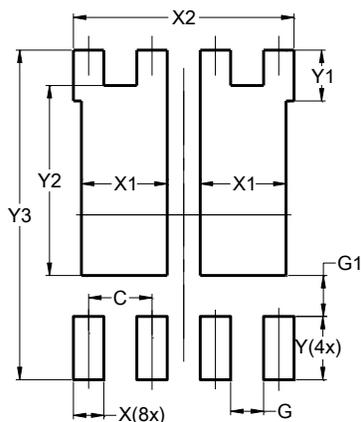
Figure 13. Transient Thermal Resistance

Package Outline Dimensions

PowerDI5060-8/SWP (Type UXD)


PowerDI5060-8/SWP (Type UXD)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	1.46	1.66	1.55
D3	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
M	3.205	4.005	3.605
W	0.025	0.225	0.125
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8/SWP (Type UXD)


Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	1.720
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610